

General Description

KEC NPT IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for soft switching application such as IH(induction heating), microwave oven, etc.

FEATURES

- High speed switching
- High system efficiency
- Soft current turn-off waveforms
- Extremely enhanced avalanche capability

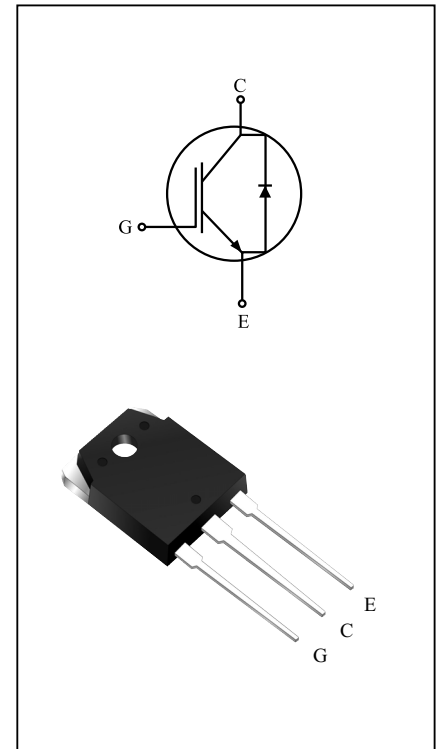
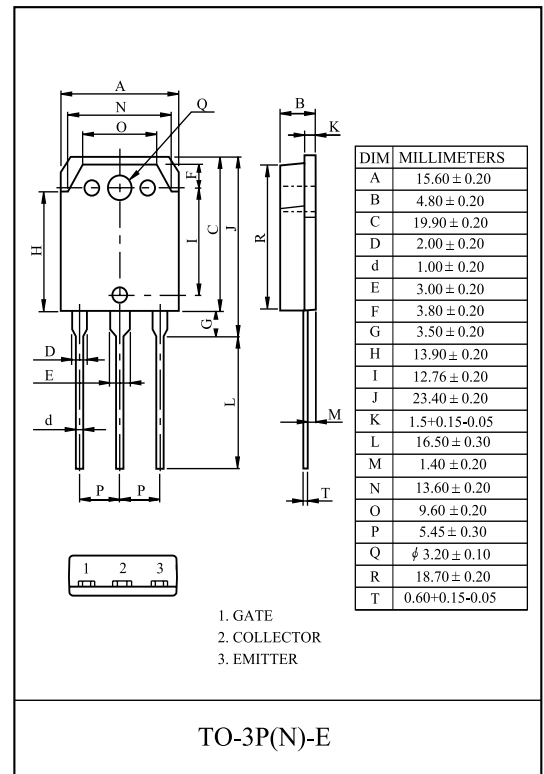
MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V_{CES}	1200	V	
Gate-Emitter Voltage		V_{GES}	± 20	V	
Collector Current	@T _C =25°C	I_C	30	A	
	@T _C =100°C		15	A	
Pulsed Collector Current		I_{CM}^*	45	A	
Diode Continuous Forward Current		@T _C =100°C	I_F	15	A
Diode Maximum Forward Current		I_{FM}	45	A	
Maximum Power Dissipation	@T _C =25°C	P_D	176	W	
	@T _C =100°C		70	W	
Maximum Junction Temperature		T_j	150	°C	
Storage Temperature Range		T_{stg}	-55 to + 150	°C	

*Repetitive rating : Pulse width limited by max. junction temperature

THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	R_{thJC}	0.92	°C/W
Thermal Resistance, Junction to Case (DIODE)	R_{thJC}	2.8	°C/W
Thermal Resistance, Junction to Ambient	R_{thJA}	40	°C/W

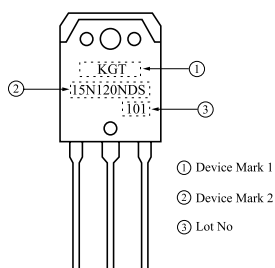


KGT15N120NDS

ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Static							
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE}=0V, I_C=1.0mA$	1200	-	-	V	
Collector Cut-off Current	I_{CES}	$V_{GE}=0V, V_{CE}=1200V$	-	-	1.0	mA	
Gate Leakage Current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$	-	-	± 100	nA	
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=15mA$	4.5	6.0	7.5	V	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=15A$	-	1.98	2.5	V	
		$V_{GE}=15V, I_C=15A, T_C = 125^\circ C$	-	2.40	-	V	
		$V_{GE}=15V, I_C=30A$	-	2.87	-	V	
Dynamic							
Total Gate Charge	Q_g	$V_{CC}=600V, V_{GE}=15V, I_C=15A$	-	70	100	nC	
Gate-Emitter Charge	Q_{ge}		-	9	-	nC	
Gate-Collector Charge	Q_{gc}		-	40	-	nC	
Turn-On Delay Time	$t_{d(on)}$	$V_{CC}=600V, I_C=15A, V_{GE}=15V, R_G=10\Omega$ Inductive Load, $T_C = 25^\circ C$	-	30	-	ns	
Rise Time	t_r		-	30	-	ns	
Turn-Off Delay Time	$t_{d(off)}$		-	120	-	ns	
Fall Time	t_f		-	150	200	ns	
Turn-On Switching Loss	E_{on}		-	2.2	-	mJ	
Turn-Off Switching Loss	E_{off}		-	0.8	-	mJ	
Total Switching Loss	E_{ts}		-	3.1	-	mJ	
Turn-On Delay Time	$t_{d(on)}$		$V_{CC}=600V, I_C=15A, V_{GE}=15V, R_G=10\Omega$ Inductive Load, $T_C = 125^\circ C$	-	35	-	ns
Rise Time	t_r			-	35	-	ns
Turn-Off Delay Time	$t_{d(off)}$			-	160	-	ns
Fall Time	t_f	-		200	-	ns	
Turn-On Switching Loss	E_{on}	-		2.5	-	mJ	
Turn-Off Switching Loss	E_{off}	-		1.5	-	mJ	
Total Switching Loss	E_{ts}	-		4.0	-	mJ	
Input Capacitance	C_{ies}	$V_{CE}=30V, V_{GE}=0V, f=1MHz$	-	1100	-	pF	
Output Capacitance	C_{oes}		-	50	-	pF	
Reverse Transfer Capacitance	C_{res}		-	30	-	pF	

Marking



KGT15N120NDS

ELECTRICAL CHARACTERISTIC OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	V_F	$I_F = 15A$	$T_C = 25^\circ C$	-	2.0	2.5	V
			$T_C = 125^\circ C$	-	2.3	-	
Diode Reverse Recovery Time	t_{rr}	$I_F = 15A$	$T_C = 25^\circ C$	-	300	-	ns
			$T_C = 125^\circ C$	-	410	-	
Diode Peak Reverse Recovery Current	I_{rr}	$I_F = 15A$ $di/dt = 200A/\mu s$	$T_C = 25^\circ C$	-	17	25	A
			$T_C = 125^\circ C$	-	18	-	
Diode Reverse Recovery Charge	Q_{rr}	$I_F = 15A$ $di/dt = 200A/\mu s$	$T_C = 25^\circ C$	-	2100	4000	nC
			$T_C = 125^\circ C$	-	3200	-	

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Fig 1. Saturation Voltage Characteristics

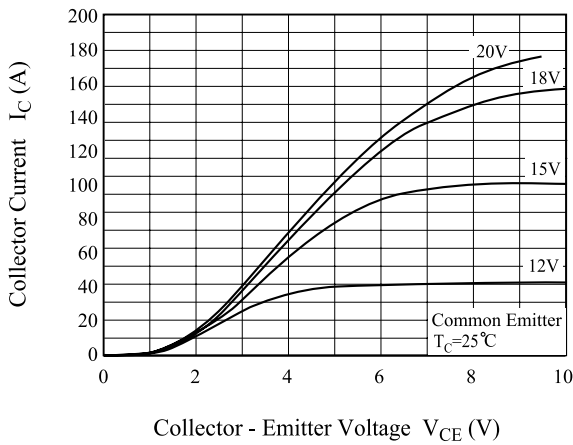


Fig 2. Saturation Voltage Characteristics

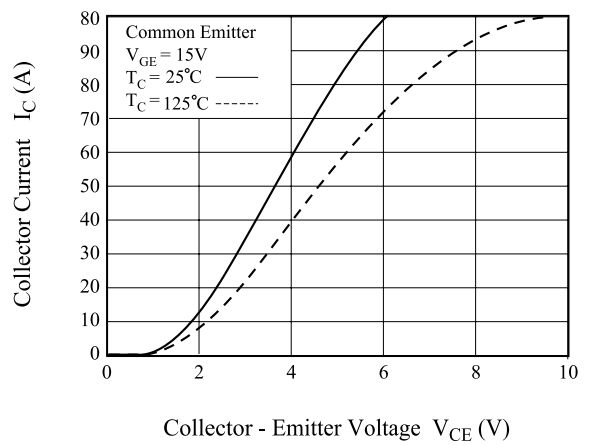


Fig 3. Saturation Voltage vs. Case Temperature

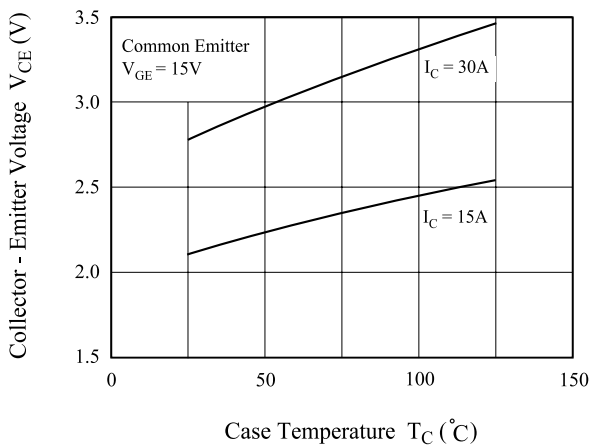


Fig 4. Saturation Voltage vs. V_{GE}

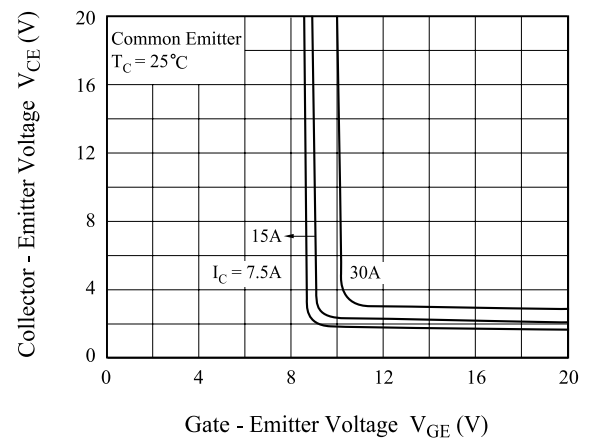


Fig 5. Saturation Voltage vs. V_{GE}

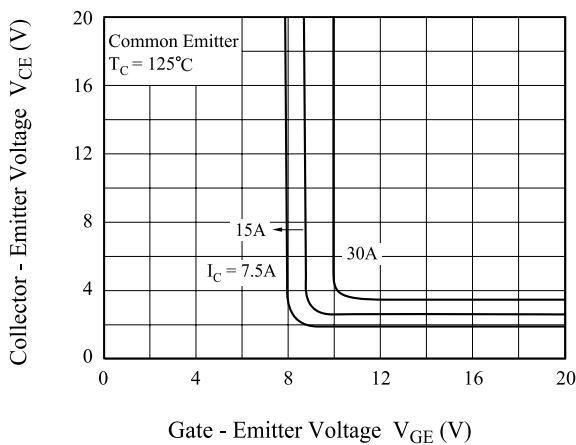
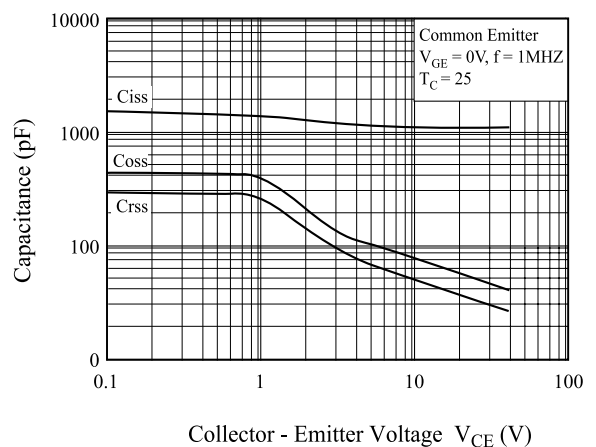


Fig 6. Capacitance Characteristics



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Fig 7. Turn-On Characteristics vs. Gate Resistance

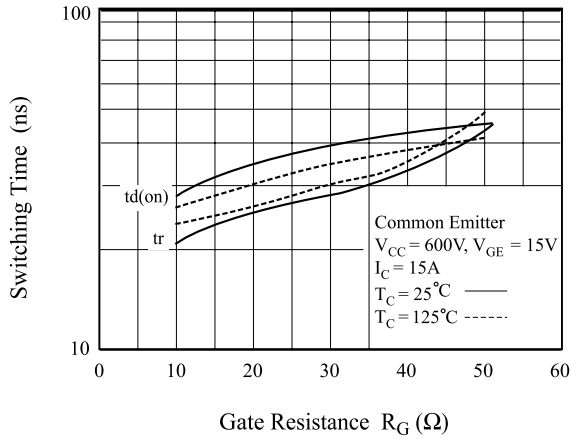


Fig 8. Turn-Off Characteristics vs. Gate Resistance

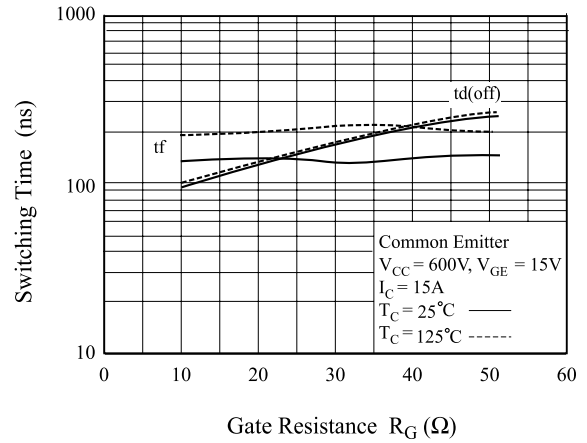


Fig 9. Switching Loss vs. Gate Resistance

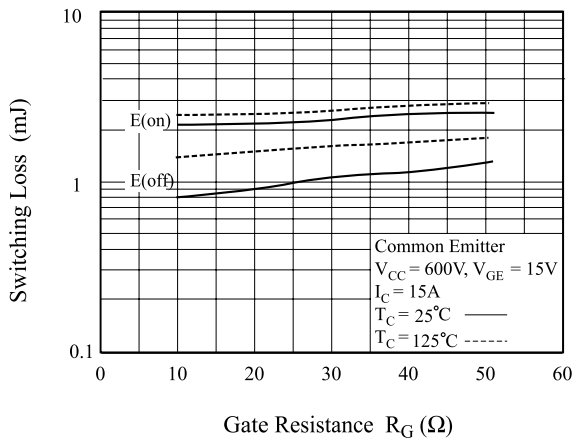


Fig 10. Turn-On Characteristics vs. Collector Current

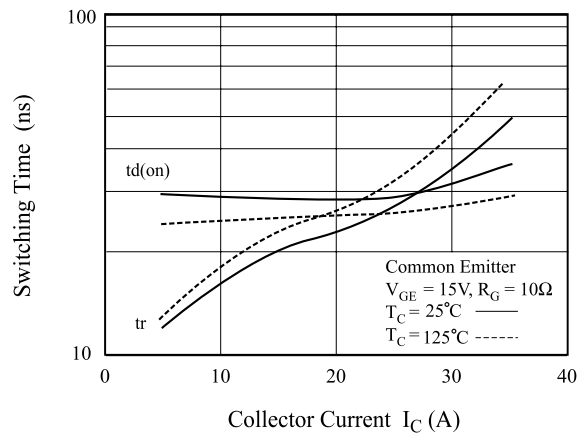


Fig 11. Turn-Off Characteristics vs. Collector Current

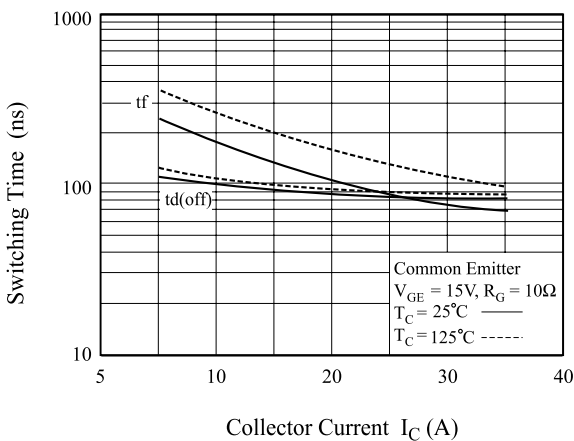
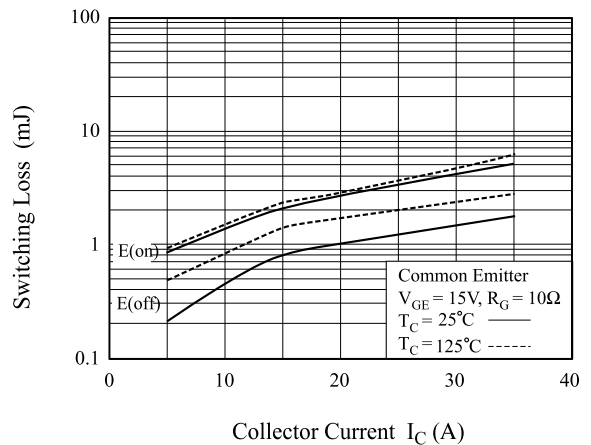


Fig 12. Switching Loss vs. Collector Current



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Fig 13. Gate Charge Characteristics

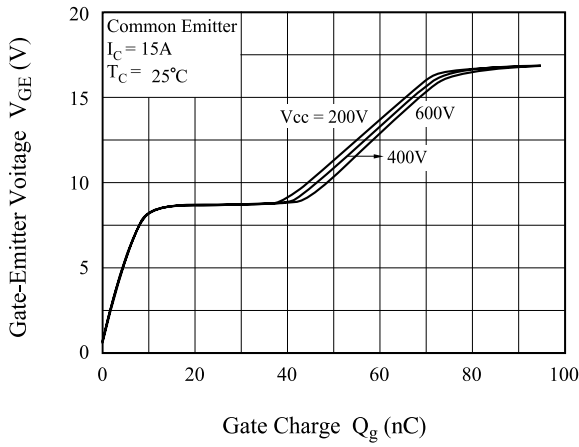


Fig 14. SOA Characteristics

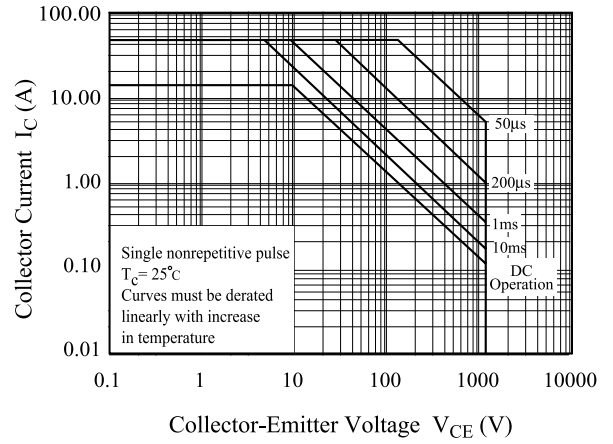


Fig 15. Turn-Off SOA

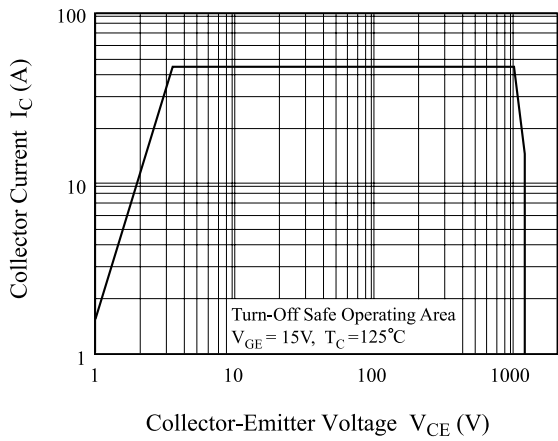
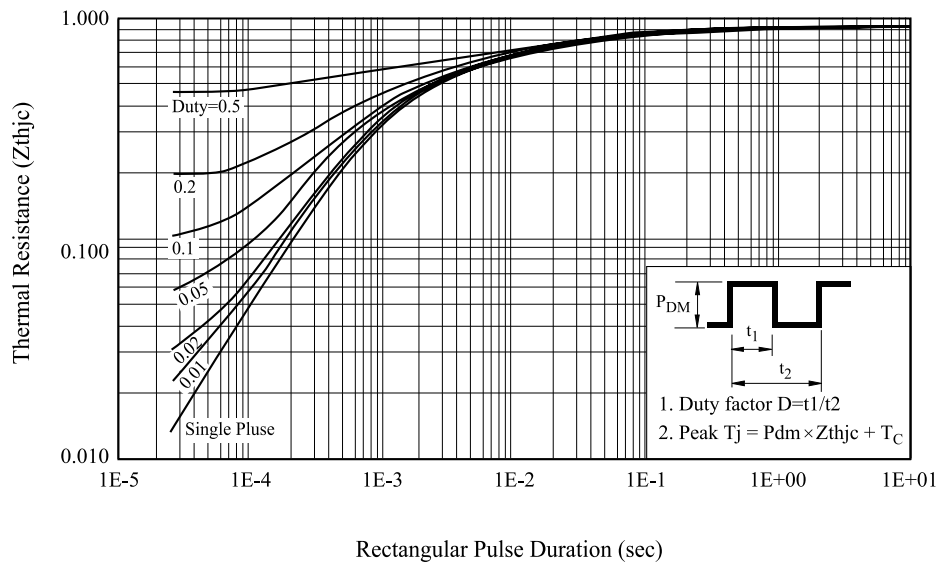


Fig 16. Transient Thermal Impedance of IGBT



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Fig 17. Forward Characteristics

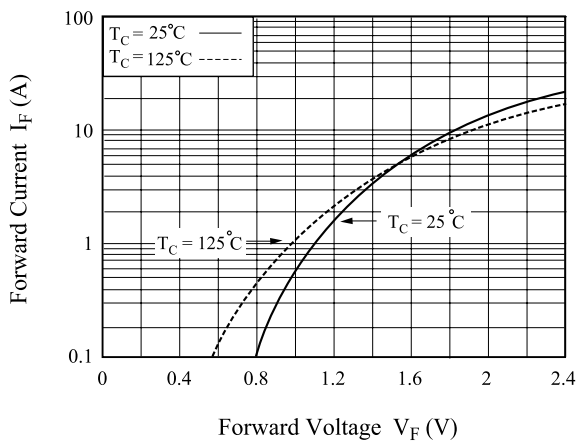


Fig 18. Reverse Recovery Current

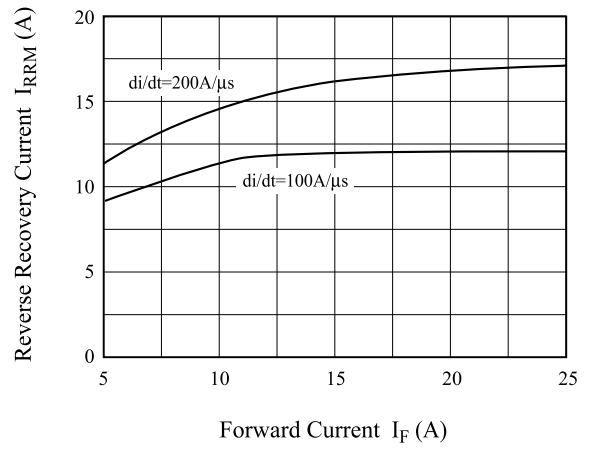


Fig 19. Reverse Recovery Time

